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(b) forming an aluminum interconnection layer on and in contact with said first insulating layer;

(c) forming a second insulating layer with said first type of stress on and in contact with said interconnection layer;

wherein said interconnection layer is sandwiched between and in contact with said first insulating layer and said second insulating layer and wherein the total stress in said insulating layers is limited to less than 2×10^5 dyne/cm so as to suppress bending of said interconnection layer.

44. (Amended) A method according to claim 43, further comprising:

(d) before forming said first insulating layer or after forming said second insulating layer, forming a third insulating layer with a second type of stress that is different from said first type of stress, so as to adjust overall stress of said stress-adjusted insulating film.

46. (Amended) A method according to claim 45, wherein the stress-adjusted insulating film has first through i-th insulating layers having the thickness t_1 through t_i , respectively, and wherein the thickness (t_i) of i-th insulating layer of said stress-adjusted film is determined so as not to exceed stress (σ_T) of said overall stress-adjusted insulating film where said stress (σ_T) is calculated as:

$$\sigma_T = \sum_{i=1}^n (t_i \times \sigma_i)$$